

# XC7WH126

Dual buffer/line driver; 3-state

Rev. 01 — 2 September 2009

Product data sheet

## 1. General description

The XC7WH126 is a high-speed Si-gate CMOS device. This device provides a dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (nOE). A LOW at nOE causes the output to assume a high-impedance OFF-state.

## 2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - ◆ HBM JESD22-A114E: exceeds 2000 V
  - ◆ MM JESD22-A115-A: exceeds 200 V
  - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from -40 °C to +125 °C

## 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
XC7WH126DP	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
XC7WH126DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
XC7WH126GD	-40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm	SOT996-2

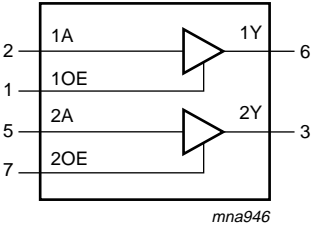
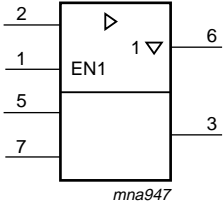
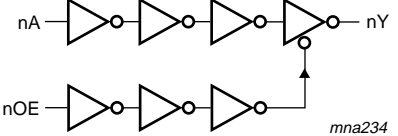
## 4. Marking

**Table 2. Marking codes**

Type number	Marking <sup>[1]</sup>
XC7WH126DP	f26
XC7WH126DC	f26
XC7WH126GD	f26

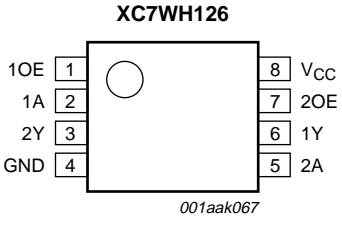
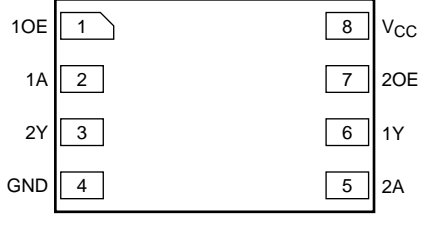
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram

 <p><i>mna946</i></p>	 <p><i>mna947</i></p>	 <p><i>mna234</i></p>
<b>Fig 1. Logic symbol</b>	<b>Fig 2. IEC logic symbol</b>	<b>Fig 3. Logic diagram (one buffer)</b>

## 6. Pinning information

### 6.1 Pinning

 <p><i>001aak067</i></p>	<p><b>XC7WH126</b></p>  <p><i>001aak068</i></p> <p>Transparent top view</p>
<b>Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)</b>	<b>Fig 5. Pin configuration SOT996-2 (XSON8U)</b>

## 6.2 Pin description

**Table 3.** Pin description

Symbol	Pin	Description
1OE, 2OE	1, 7	output enable input (active LOW)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V <sub>CC</sub>	8	supply voltage

## 7. Functional description

**Table 4.** Function table<sup>[1]</sup>

Control	Input	Output
nOE	nA	nY
H	L	L
H	H	H
L	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

## 8. Limiting values

**Table 5.** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
V <sub>I</sub>	input voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V	[1] -20	-	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V	[1] -	±20	mA
I <sub>O</sub>	output current	-0.5 V < V <sub>O</sub> < V <sub>CC</sub> + 0.5 V	-	±25	mA
I <sub>CC</sub>	supply current		-	75	mA
I <sub>GND</sub>	ground current		-75	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.  
 For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.  
 For XSON8U package: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	5.5	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 3.3 V ± 0.3 V	-	-	100	ns/V
		V <sub>CC</sub> = 5.0 V ± 0.5 V	-	-	20	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V <sub>CC</sub> = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I <sub>O</sub> = -8.0 mA; V <sub>CC</sub> = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I <sub>O</sub> = 8.0 mA; V <sub>CC</sub> = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I <sub>OZ</sub>	OFF-state output current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	0.25	-	2.5	-	10	μA
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	1.0	-	10	-	40	μA
C <sub>I</sub>	input capacitance		-	1.5	10	-	10	-	10	pF

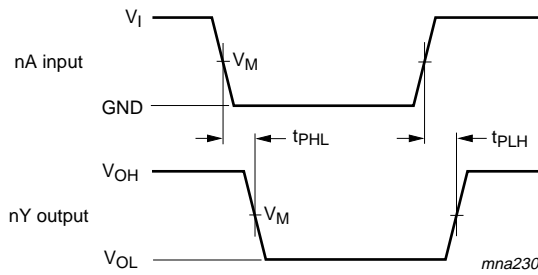
## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**  
*GND = 0 V; for test circuit see Figure 8.*

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 6	[1]							
		V <sub>CC</sub> = 3.0 V to 3.6 V	[2]							
		C <sub>L</sub> = 15 pF	-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		C <sub>L</sub> = 50 pF	-	6.6	11.5	1.0	13.0	1.0	14.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	[3]							
		C <sub>L</sub> = 15 pF	-	3.4	5.5	1.0	6.5	1.0	7.0	ns
t <sub>en</sub>	enable time	nOE to nY; see Figure 7	[1]							
		V <sub>CC</sub> = 3.0 V to 3.6 V	[2]							
		C <sub>L</sub> = 15 pF	-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		C <sub>L</sub> = 50 pF	-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	[3]							
		C <sub>L</sub> = 15 pF	-	3.6	5.1	1.0	6.0	1.0	6.5	ns
t <sub>dis</sub>	disable time	nOE to nY; see Figure 7	[1]							
		V <sub>CC</sub> = 3.0 V to 3.6 V	[2]							
		C <sub>L</sub> = 15 pF	-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		C <sub>L</sub> = 50 pF	-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	[3]							
		C <sub>L</sub> = 15 pF	-	4.1	6.8	1.0	8.0	1.0	8.5	ns
C <sub>PD</sub>	power dissipation capacitance	per buffer; C <sub>L</sub> = 50 pF; f <sub>i</sub> = 1 MHz; V <sub>1</sub> = GND to V <sub>CC</sub>	[4]	-	10	-	-	-	-	pF

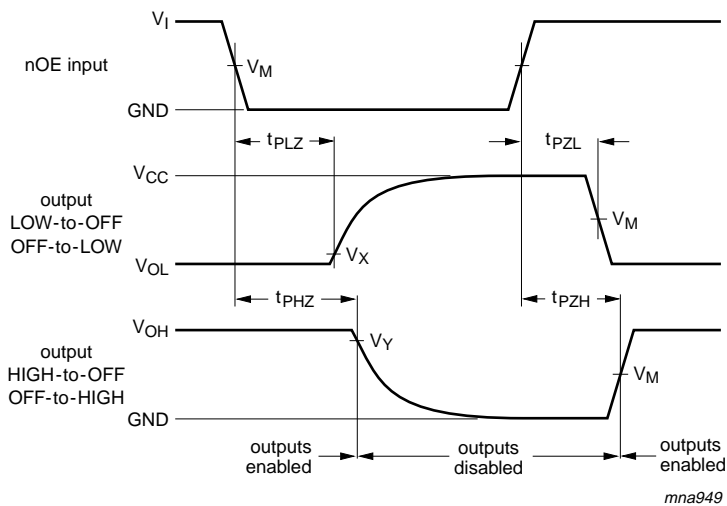
- [1] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.  
t<sub>en</sub> is the same as t<sub>PZL</sub> and t<sub>PZH</sub>.  
t<sub>dis</sub> is the same as t<sub>PLZ</sub> and t<sub>PHZ</sub>.
- [2] Typical values are measured at V<sub>CC</sub> = 3.3 V.
- [3] Typical values are measured at V<sub>CC</sub> = 5.0 V.
- [4] C<sub>PD</sub> is used to determine the dynamic power dissipation P<sub>D</sub> (μW).  
P<sub>D</sub> = C<sub>PD</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>i</sub> + Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) where:  
f<sub>i</sub> = input frequency in MHz;  
f<sub>o</sub> = output frequency in MHz;  
C<sub>L</sub> = output load capacitance in pF;  
V<sub>CC</sub> = supply voltage in V.

**12. Waveforms**



Measurement points are given in [Table 9](#).  
 Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

**Fig 6. Input (nA) to output (nY) propagation delays**



Measurement points are given in [Table 9](#).  
 Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

**Fig 7. Enable and disable times**

**Table 9. Measurement points**

Type	Input	Output		
	$V_M$	$V_M$	$V_X$	$V_Y$
XC7WH126	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$



Test data is given in [Table 10](#).

Definitions test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_L$  = Load resistance.

S1 = Test selection switch.

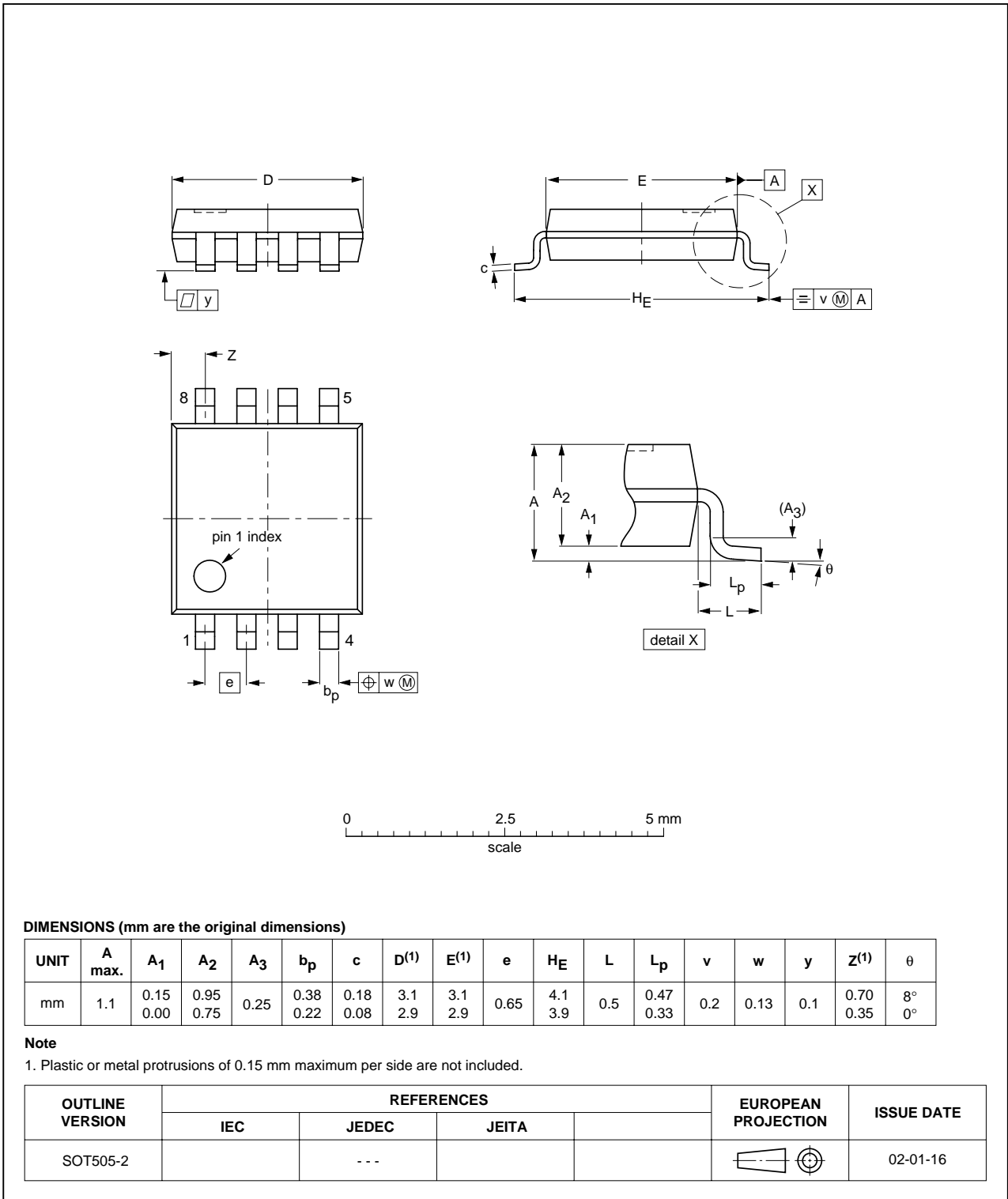
**Fig 8. Test circuit for measuring switching times**

**Table 10. Test data**

Type	Input		Load		S1 position		
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
XC7WH126	$V_{CC}$	$\leq 3$ ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$

**13. Package outline**

**TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2**



**Fig 9. Package outline SOT505-2 (TSSOP8)**



VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

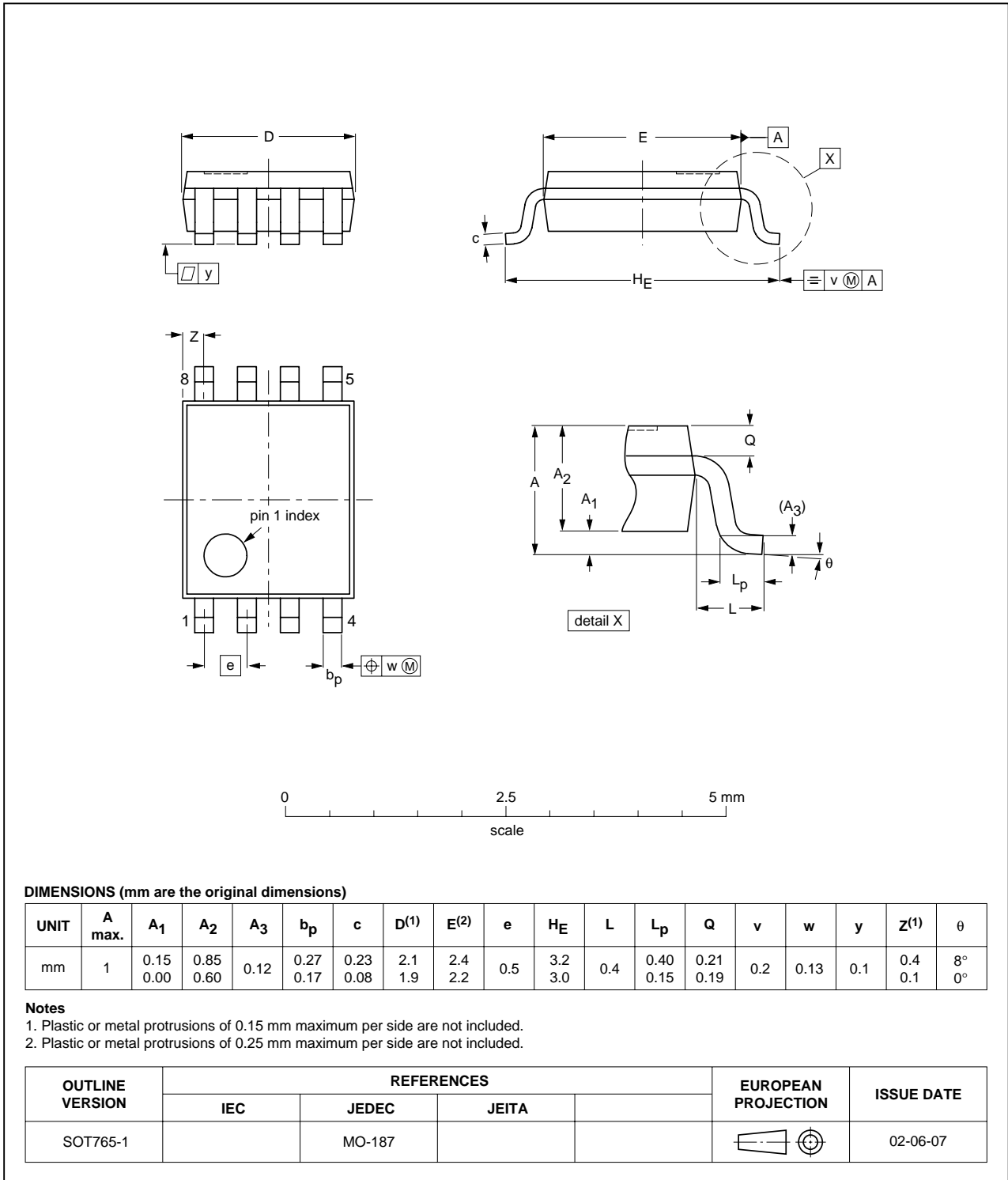


Fig 10. Package outline SOT765-1 (VSSOP8)

**XSON8U: plastic extremely thin small outline package; no leads;  
8 terminals; UTLP based; body 3 x 2 x 0.5 mm**

**SOT996-2**



**Fig 11. Package outline SOT996-2 (XSON8U)**

## 14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

## 15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
XC7WH126_1	20090902	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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